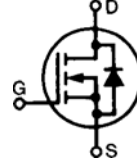


High Voltage Power MOSFETs

N-Channel Enhancement Mode
Avalanche Rated, High dv/dt

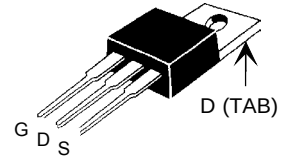
IXTA/IXTP 3N120
IXTA/IXTP 3N110

V_{DSS}	I_{D25}	$R_{DS(on)}$
1200 V	3 A	4.5 Ω
1100 V	3 A	4.0 Ω

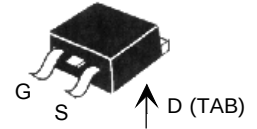


Symbol	Test Conditions	Maximum Ratings		
V_{DSS}	$T_J = 25^\circ\text{C}$ to 150°C	3N120	1200	V
		3N110	1100	V
V_{DGR}	$T_J = 25^\circ\text{C}$ to 150°C ; $R_{GS} = 1\text{ M}\Omega$	3N120	1200	V
		3N110	1100	V
V_{GS}	Continuous		± 20	V
V_{GSM}	Transient		± 30	V
I_{D25}	$T_C = 25^\circ\text{C}$		3	A
I_{DM}	$T_C = 25^\circ\text{C}$, pulse width limited by T_{JM}		12	A
I_{AR}	$T_C = 25^\circ\text{C}$		3	A
E_{AR}	$T_C = 25^\circ\text{C}$		20	mJ
E_{AS}			700	mJ
dv/dt	$I_S \leq I_{DM}$, $di/dt \leq 100\text{ A}/\mu\text{s}$, $V_{DD} \leq V_{DSS}$, $T_J \leq 150^\circ\text{C}$, $R_G = 2\text{ }\Omega$		5	V/ns
P_D	$T_C = 25^\circ\text{C}$		150	W
T_J			-55 to +150	$^\circ\text{C}$
T_{JM}			150	$^\circ\text{C}$
T_{stg}			-55 to +150	$^\circ\text{C}$
T_L	1.6 mm (0.063 in) from case for 10 s		300	$^\circ\text{C}$
M_d	Mounting torque (TO-220)		1.13/10	Nm/lb.in.
Weight	TO-220		4	g
	TO-263		2	g

TO-220 (IXTP)



TO-263 (IXTA)



G = Gate
S = Source

D = Drain
TAB = Drain

Features

- International standard packages
- Low $R_{DS(on)}$
- Rated for unclamped Inductive load Switching (UIS)
- Molding epoxies meet UL 94 V-0 flammability classification

Advantages

- Easy to mount
- Space savings
- High power density

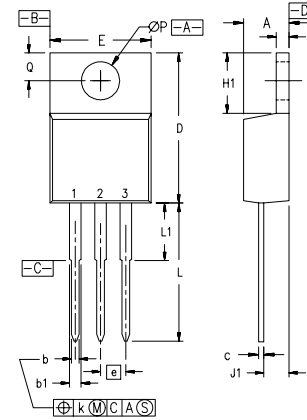
Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
V_{DSS}	$V_{GS} = 0\text{ V}$, $I_D = 1\text{ mA}$	3N120 1200 3N110 1100		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 250\text{ }\mu\text{A}$	2.5		4.5 V
I_{GSS}	$V_{GS} = \pm 20\text{ V}_{DC}$, $V_{DS} = 0$			$\pm 100\text{ nA}$
I_{DSS}	$V_{DS} = 0.8\text{ V}_{DSS}$, $V_{GS} = 0\text{ V}$	$T_J = 25^\circ\text{C}$ $T_J = 125^\circ\text{C}$		25 μA 1 mA
$R_{DS(on)}$	$V_{GS} = 10\text{ V}$, $I_D = 0.5\text{ I}_{D25}$ Note 1	3N120 3N110		4.5 Ω 4.0 Ω

Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
g_{fs}	$V_{DS} = 10\text{ V}; I_D = 0.5 \cdot I_{D25}$, Note 1	1.5	2.2	S
C_{iss}	$V_{GS} = 0\text{ V}, V_{DS} = 25\text{ V}, f = 1\text{ MHz}$	1050	1300	pF
C_{oss}		100	125	pF
C_{rss}		25	50	pF
$t_{d(on)}$	$V_{GS} = 10\text{ V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 0.5 \cdot I_{D25}$ $R_G = 4.7\ \Omega$ (External),	17		ns
t_r		15		ns
$t_{d(off)}$		32		ns
t_f		18		ns
$Q_{g(on)}$	$V_{GS} = 10\text{ V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 0.5 \cdot I_{D25}$	39		nC
Q_{gs}		9		nC
Q_{gd}		22		nC
R_{thJC}	(TO-220)		0.8	K/W
R_{thCK}		0.25		K/W

Source-Drain Diode		Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
Symbol	Test Conditions	min.	typ.	max.
I_S	$V_{GS} = 0\text{ V}$			3 A
I_{SM}	Repetitive; pulse width limited by T_{JM}			12 A
V_{SD}	$I_F = I_S, V_{GS} = 0\text{ V}$, Note 1			1.5 V
t_{rr}	$I_F = I_S, -di/dt = 100\text{ A}/\mu\text{s}, V_R = 100\text{ V}$	700		ns

Notes: 1. Pulse test, $t \leq 300\ \mu\text{s}$, duty cycle $d \leq 2\%$

TO-220 (IXTP) Outline

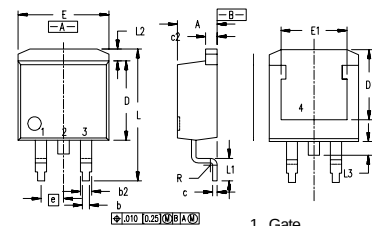


Pins: 1 - Gate
2 - Drain
3 - Source
4 - Drain
Bottom Side

SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.170	.190	4.32	4.83
b	.025	.040	0.64	1.02
b1	.045	.065	1.15	1.65
c	.014	.022	0.35	0.56
D	.580	.630	14.73	16.00
E	.390	.420	9.91	10.66
e	.100 BSC		2.54 BSC	
F	.045	.055	1.14	1.40
H1	.230	.270	5.85	6.85
J1	.090	.110	2.29	2.79
k	0	.015	0	0.38
L	.500	.550	12.70	13.97
L1	.110	.230	2.79	5.84
ØP	.139	.161	3.53	4.08
Q	.100	.125	2.54	3.18

NOTE: This drawing will meet all dimensions requirement of JEDEC outline TO-220 AB.

TO-263 (IXTA) Outline



1. Gate
2. Drain
3. Source
4. Drain
Bottom Side

Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.06	4.83	.160	.190
A1	2.03	2.79	.080	.110
b	0.51	0.99	.020	.039
b2	1.14	1.40	.045	.055
c	0.46	0.74	.018	.029
c2	1.14	1.40	.045	.055
D	8.64	9.65	.340	.380
D1	7.11	8.13	.280	.320
E	9.65	10.29	.380	.405
E1	6.86	8.13	.270	.320
e	2.54	BSC	.100	BSC
L	14.61	15.88	.575	.625
L1	2.29	2.79	.090	.110
L2	1.02	1.40	.040	.055
L3	1.27	1.78	.050	.070
L4	0	0.38	0	.015
R	0.46	0.74	.018	.029

IXYS reserves the right to change limits, test conditions, and dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:	4,835,592	4,881,106	5,017,508	5,049,961	5,187,117	5,486,715	6,306,728B1
	4,850,072	4,931,844	5,034,796	5,063,307	5,237,481	5,381,025	

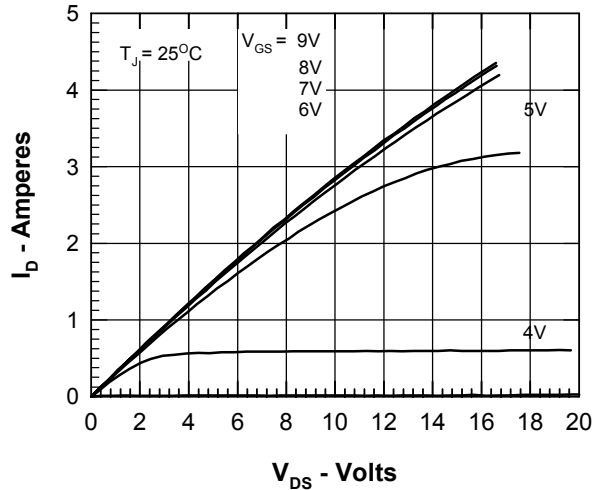


Fig.1 Output Characteristics @ $T_J = 25^\circ\text{C}$

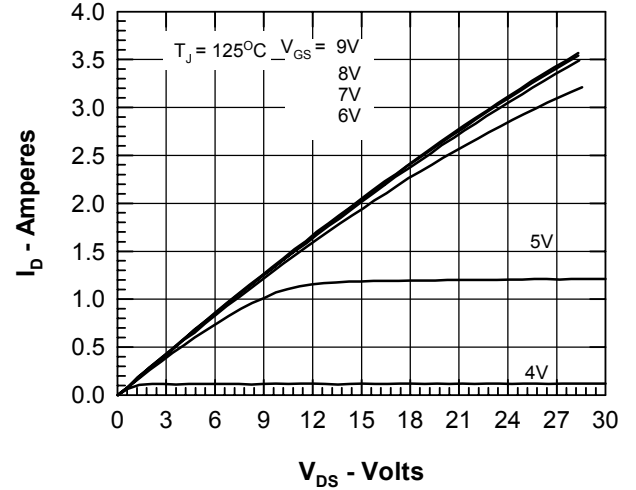


Fig. 2 Output Characteristics @ $T_J = 125^\circ\text{C}$

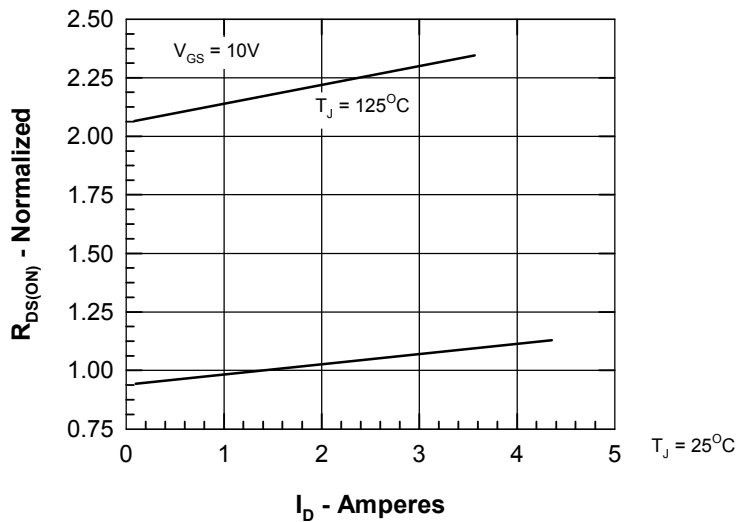


Fig. 3 $R_{DS(on)}$ vs. Drain Current

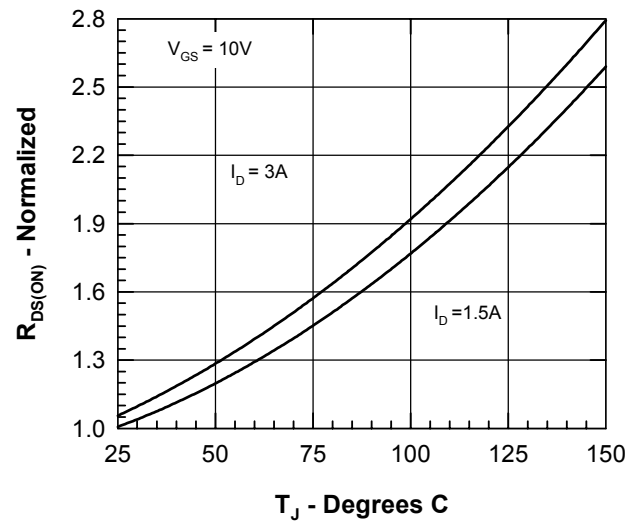


Fig.4 Temperature Dependence of Drain to Source Resistance

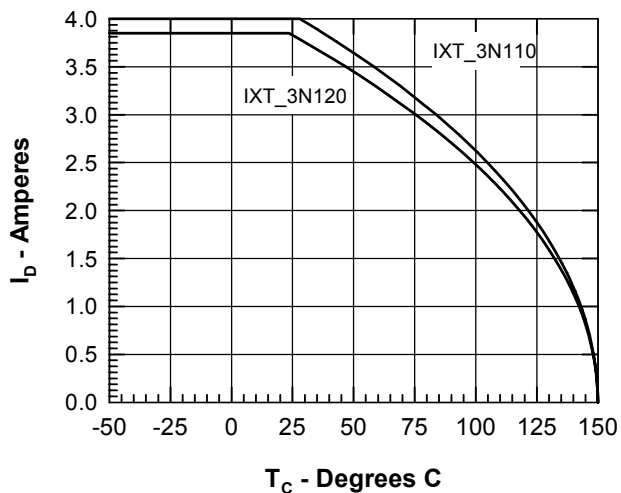


Fig. 5 Drain Current vs. Case Temperature

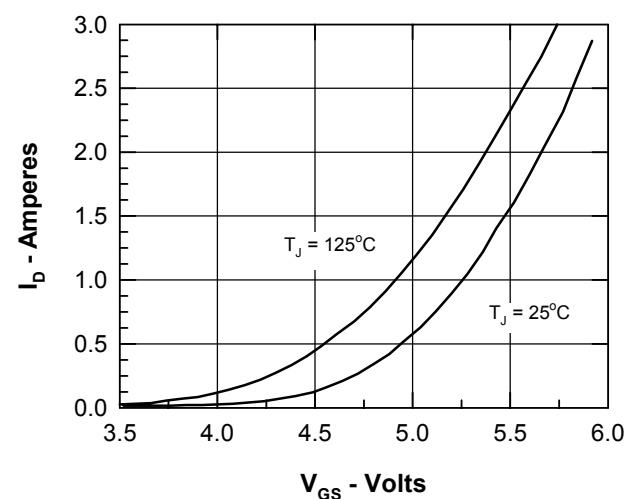


Fig. 6 Admittance Curves

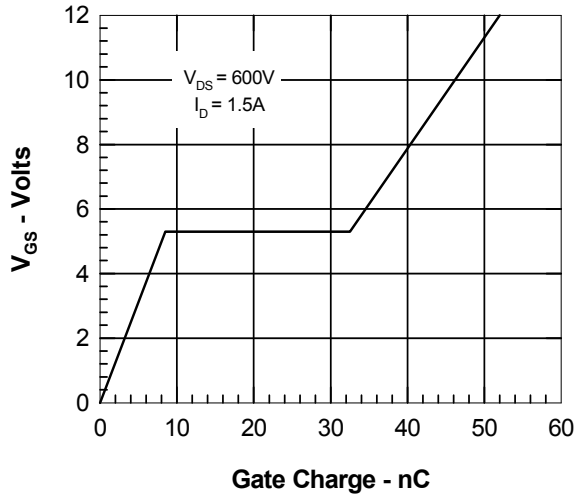


Fig. 7 Gate Charge Characteristic Curve

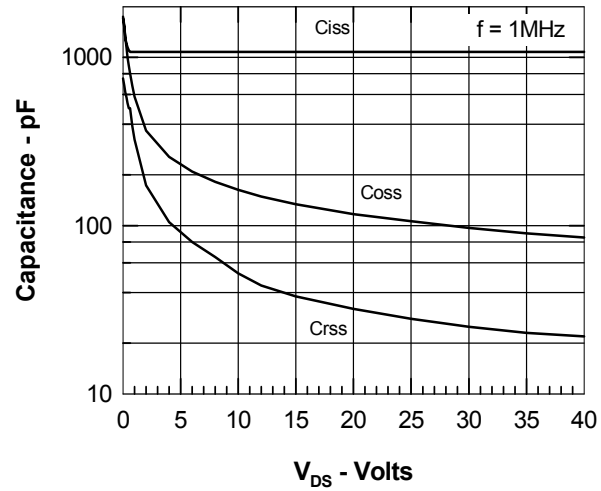


Fig. 8 Capacitance Curves

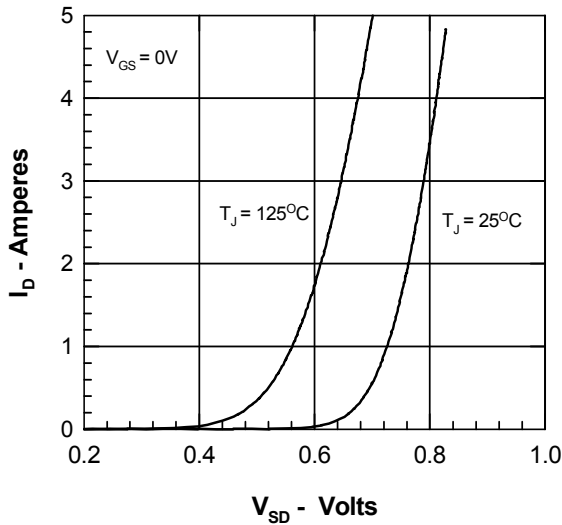


Fig. 9 Drain Current vs Drain to Source Voltage

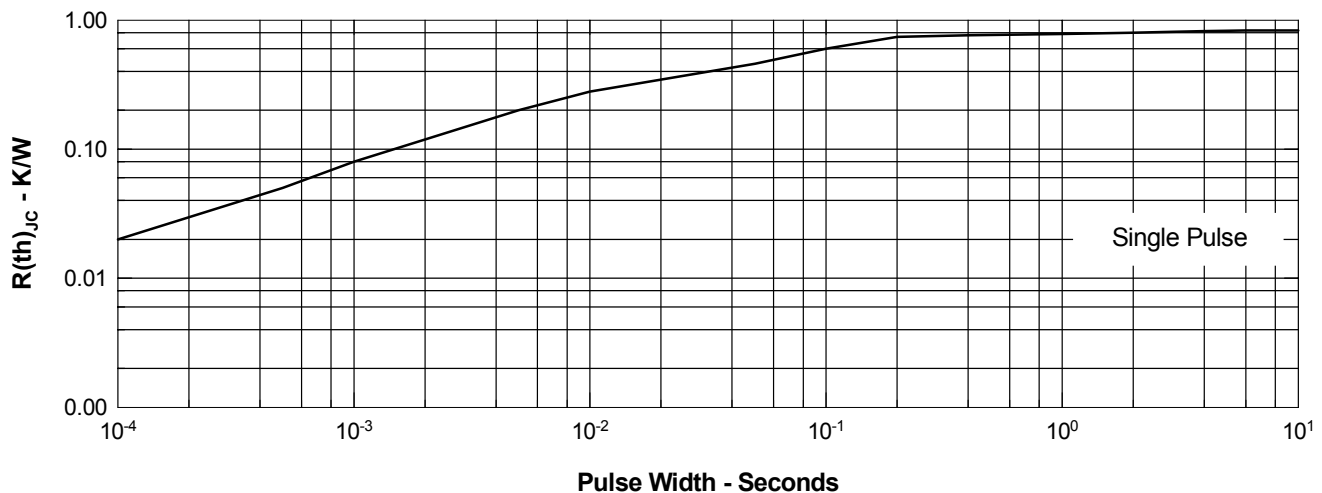


Fig.10 Transient Thermal Impedance